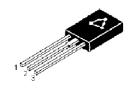
PNP Transistor TO-126







Pin Configuration:

- 1. Emitter
- 2. Collector
- 3. Base

Feature:

- PNP Plastic Power Transistors
- · Medium Power Linear and Switching Applications

Absolute Maximum Ratings

Description	Symbol	-	BD140	Unit
Collector-Base Voltage (Open Emitter)	V _{CBO}		100	V
Collector Emitter Voltage (Open Base)	V _{CEO}		80	V
Collector Current	I _C		1.5	А
Total Power Dissipation upto T _C = 25°C	P _{tot}	Max.	12.5	W
Junction Temperature	T _j		150	°C
Collector-Emitter Saturation Voltage I _C = 0.5A, I _B = 0.05A	V _{CE (Sat)}		0.5	V
DC Current Gain I _C = 0.15A; V _{CE} = 2V	h _{FE}	Min. Max.	40 250	-

Ratings (at $T_a = 25$ °C unless otherwise specified)

Description	Symbol	-	BD140	Unit
Collector-Base Voltage (Open Emitter)	V _{CBO}		100	
Collector Emitter Voltage (Open Base)	V_{CEO}		80	V
Emitter-Base Voltage (Open Collector)	V _{EBO}		5	
Collector Current	I _C	Max.	1.5	А
Base Current	I _B		0.5	A
Total Power Dissipation up to T _A = 25°C Derate above 25°C	P _{tot}		1.25 10	W mW/°C

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Ratings (at $T_a = 25$ °C unless otherwise specified)

Description	Symbol	-	BD140	Unit
Total Power Dissipation up to T _C = 25°C Derate above 25°C	P _{tot}	Max.	12.5 100	W mW/°C
Junction Temperature	T _j		150	°C
Storage Temperature	T _{stg}	-	-65 to +150	C

Thermal Resistance

From Junction to Case	R _{th (j-c)}	-	10	°C/W
From Junction to Ambient	R _{th (j-a)}	-	100	C/VV

Characteristics ($T_a = 25$ °C unless otherwise specified)

Description	Symbol	-	BD140	Unit
Collector Cut off Current $I_E = 0$; $V_{CB} = 30V$ $I_E = 0$; $V_{CB} = 30V$; $T_C = 125$ °C	I _{СВО}	Max.	0.1 10	μA
Emitter Cut off Current I _C = 0; V _{EB} = 5V	I _{EBO}		10	
Breakdown Voltages $I_C = 0.03A$; $I_B = 0$ $I_C = 1mA$; $I_E = 0$ $I_E = 1mA$; $I_C = 0$	V _{CEO (Sus)} * V _{CBO} V _{EBO}	Min.	80 100 5	
Saturation Voltage $I_C = 0.5A$; $I_B = 0.05A$	V _{CE (sat)} *	Max.	0.5	V
Base-Emitter On Voltage $I_C = 0.5A; V_{CE} = 2V$	V _{BE (on)} *	iviax.	1	
DC Current Gain I _C = 0.15A; V _{CE} = 2V**	h _{FE} *	Min. Max.	40 250	-

** hFE Classification:

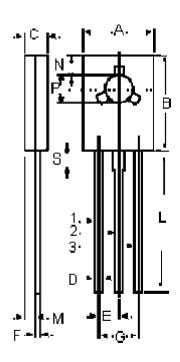
-6	Min.	40
	Max.	100
-10	Min.	63
	Max.	160
-16	Min.	100
	Max.	250
-25	Min.	160
	Max.	400

^{*} Pulse Test: Pulse Width = ≤300μs, Duty Cycle ≤2%.



PNP Transistor TO-126





Pin Configuration:

- 1. Emitter
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Dimensions	Min.	Max.
А	7.4	7.8
В	10.5	10.8
С	2.4	2.7
D	0.7	0.9
E	2.25 (Typical)	
F	0.49	0.75
G	4.5 (Typical)	
L	15.7 (Typical)	
М	1.27 (Typical)	
N	3.75 (Typical)	
Р	3	3.2
S	2.5 (Typical)	

Dimensions: Millimetres

Part Number Table

Description	Part Number	
Transistor, PNP, TO-126	BD140	

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